

# RJK4006DPD

# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1547-0100 Rev.1.00 Dec 19, 2008

### **Features**

- Low on-resistance
- Low leakage current
- High speed switching

### **Outline**

RENESAS Package code: PRSS0004ZG-A (Package name: MP-3A) 1. Gate 2. Drain 3. Source 4. Drain

## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

H	0.1.1		(1a - 23 C)		
Item	Symbol	Ratings	Unit		
Drain to source voltage	$V_{DSS}$	400	V		
Gate to source voltage	$V_{GSS}$	±30	V		
Drain current	I <sub>D</sub> Note4	8	А		
Drain peak current	I <sub>D (pulse)</sub> Note1	24	Α		
Body-drain diode reverse drain current	I <sub>DR</sub>	8	А		
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	24	Α		
Avalanche current	I <sub>AP</sub> Note3	8	Α		
Avalanche energy	E <sub>AR</sub> Note3	3.7	mJ		
Channel dissipation	Pch Note2	65	W		
Channel to case thermal impedance	θch-c	1.92	°C/W		
Channel temperature	Tch	150	°C		
Storage temperature	Tstg	-55 to +150	°C		

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C
- 4. Limited by maximum safe operation area

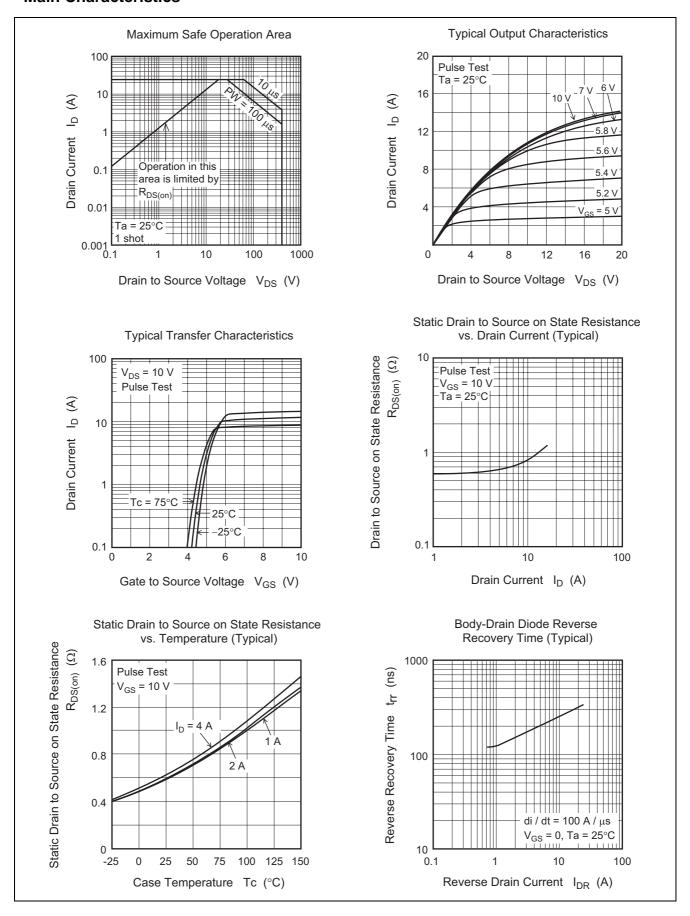
## **Electrical Characteristics**

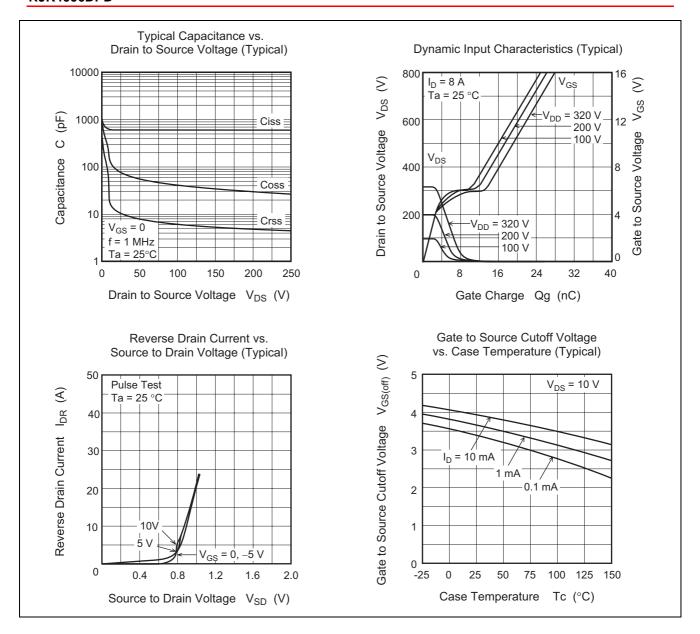
 $(Ta = 25^{\circ}C)$ 

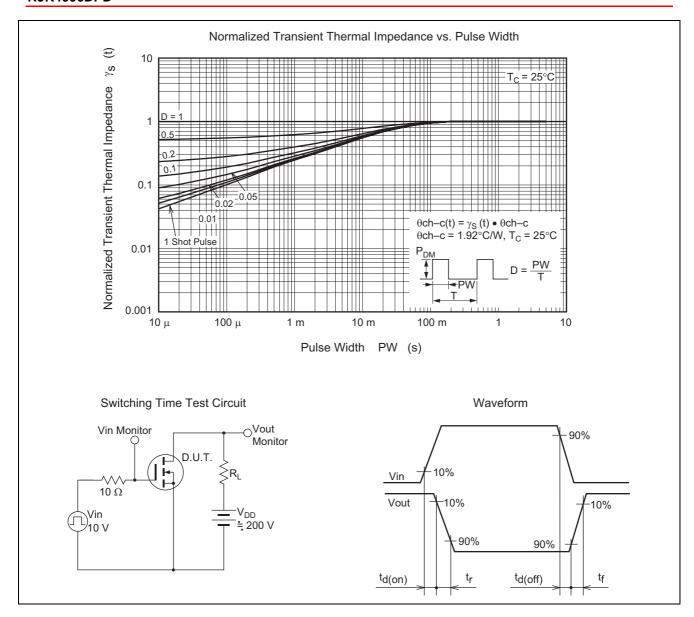
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	400	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 400 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	_	0.69	0.80	Ω	$I_D = 4 \text{ A}, V_{GS} = 10 \text{ V}^{Note5}$
Input capacitance	Ciss	_	620	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	80	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	11	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	30	_	ns	I <sub>D</sub> = 4 A
Rise time	t <sub>r</sub>	_	30	_	ns V <sub>GS</sub> = 10 V	V <sub>GS</sub> = 10 V
Turn-off delay time	$t_{d(off)}$	_	60	_	ns	$R_L = 50 \Omega$
Fall time	t <sub>f</sub>	_	20	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	20	_	nC	V <sub>DD</sub> = 320 V
Gate to source charge	Qgs	_	4	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	9	_	nC	I <sub>D</sub> = 8 A
Body-drain diode forward voltage	$V_{DF}$	_	0.9	1.5	V	$I_F = 8 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	230	_	ns	$I_F = 8 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 5. Pulse test

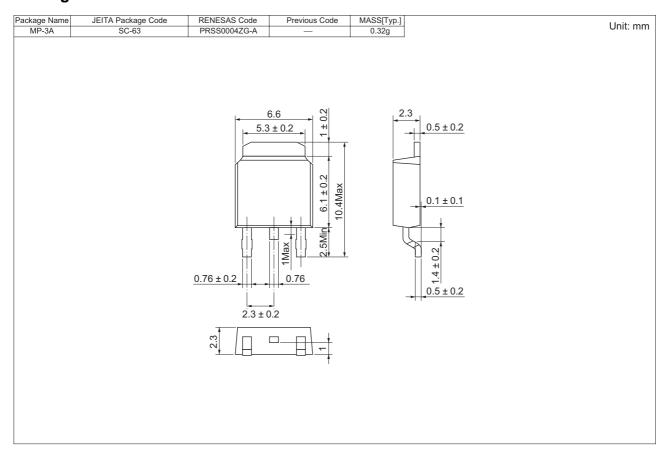
### **Main Characteristics**







## **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container		
RJK4006DPD-00-J2	3000 pcs	Taping		

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